

Vishay Siliconix

## N-Channel 150 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)		
150	0.095 at V <sub>GS</sub> = 10 V	15		
	0.100 at V <sub>GS</sub> = 6 V	15		

TO-252

GDS

Top View

Ordering Information: SUD15N15-95-E3 (Lead (Pb) free)

Drain Connected to Tab

#### FEATURES

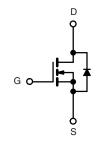
- TrenchFET<sup>®</sup> Power MOSFETS
- 175 °C Junction Temperature
- 100 % R<sub>g</sub> Tested



 Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### **APPLICATIONS**

• Primary Side Switch



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)					
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	150	V	
Gate-Source Voltage		V <sub>GS</sub>	± 20		
Continuous Drain Current (T <sub>.1</sub> = 175 °C) <sup>b</sup>	T <sub>C</sub> = 25 °C	L	15		
Continuous Drain Current $(T_j = 175^{\circ}C)^2$	T <sub>C</sub> = 125 °C		8.7		
Pulsed Drain Current	I <sub>DM</sub>	25	А		
Continuous Source Current (Diode Conduction)		۱ <sub>s</sub>	15		
Avalanche Current		I <sub>AR</sub>	15		
Repetitive Avalanche Energy (Duty Cycle $\leq$ 1 %)	L = 0.1 mH	E <sub>AR</sub>	11.3	mJ	
Maximum Dawar Dissinction	T <sub>C</sub> = 25 °C	P <sub>D</sub>	62 <sup>b</sup>	w	
Maximum Power Dissipation	T <sub>A</sub> = 25 °C		2.7 <sup>a</sup>		
Operating Junction and Storage Temperature Range	·	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
hunstion to Ambienta	t ≤ 10 s	R <sub>thJA</sub>	16	20	°C/W	
Junction-to-Ambient <sup>a</sup>	Steady State		45	55		
Junction-to-Case		R <sub>thJC</sub>	2	2.4		

Notes:

a. Surface mounted on 1" x 1" FR4 board.

b. See SOA curve for voltage derating.

r teenineal questions, contact. <u>priosteensupport @ VISIAy</u>

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Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 V, I_D = 250 \mu A$	150			v	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	2			v	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
		V <sub>DS</sub> = 120 V, V <sub>GS</sub> = 0 V			1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 120 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{\text{J}} = 125 ^{\circ}\text{C}$			50	μΑ	
		$V_{DS}$ = 120 V, $V_{GS}$ = 0 V, $T_{J}$ = 175 °C			250		
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 V, V_{GS} = 10 V$	25			А	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A	0.077 0.09		0.095		
- · · · · · · · · · · · · · · · · · · ·	Б	$V_{GS}$ = 10 V, I <sub>D</sub> = 15 A, T <sub>J</sub> = 125 °C			0.190		
Drain-Source On-State Resistance <sup>b</sup>	R <sub>DS(on)</sub>	$V_{GS}$ = 10 V, I <sub>D</sub> = 15 A, T <sub>J</sub> = 175 °C			0.250	Ω	
		$V_{GS} = 6 \text{ V}, \text{ I}_{D} = 10 \text{ A}$		0.081	0.100	1	
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 15 A		25		S	
<b>Dynamic</b> <sup>a</sup>		· · · · · · · · · · · · · · · · · · ·		•			
Input Capacitance	C <sub>iss</sub>			900		pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$ , $V_{DS} = 25 V$ , f = 1 MHz		115			
Reverse Transfer Capacitance	C <sub>rss</sub>			70			
Total Gate Charge <sup>c</sup>	Qg			20	25		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS}$ = 75 V, $V_{GS}$ = 10 V, $I_{D}$ = 15 A		5.5		nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			7			
Gate Resistance	Rg		1		3.2	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			8	12		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = 75 V, $R_L$ = 5 $\Omega$		35	55		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong$ 15 A, $V_{GEN}$ = 10 V, $R_G$ = 2.5 $\Omega$		17	25	ns	
Fall Time <sup>c</sup>	t <sub>f</sub>			30	45		
Source-Drain Diode Ratings and Cha	racteristic (T	r <sub>C</sub> = 25 °C)					
Pulsed Current	I <sub>SM</sub>				25	А	
Diode Forward Voltage <sup>b</sup>	V <sub>SD</sub>	I <sub>F</sub> = 15 A, V <sub>GS</sub> = 0 V		0.9	1.5	V	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 15 A, dl/dt = 100 A/μs		55	85	ns	

Notes:

a. Guaranteed by design, not subject to production testing.

b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

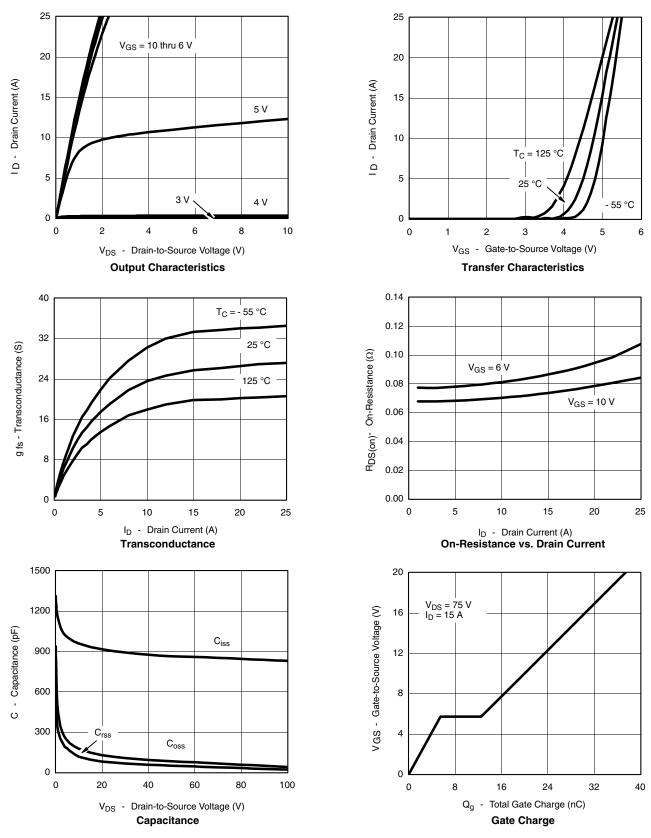
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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#### TYPICAL CHARACTERISTICS (25 °C unless noted)

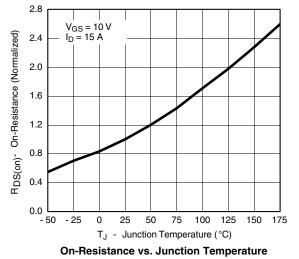


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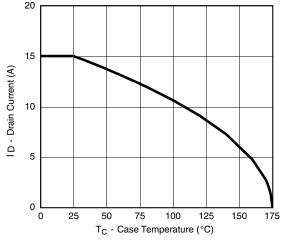
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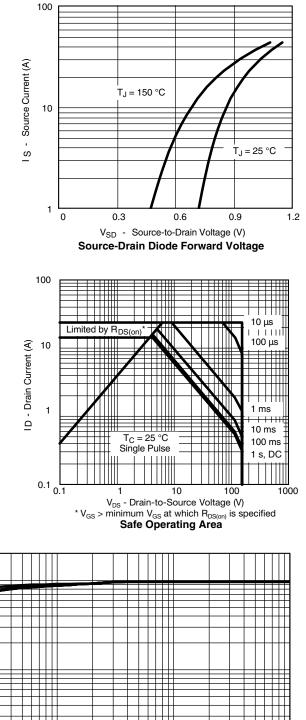
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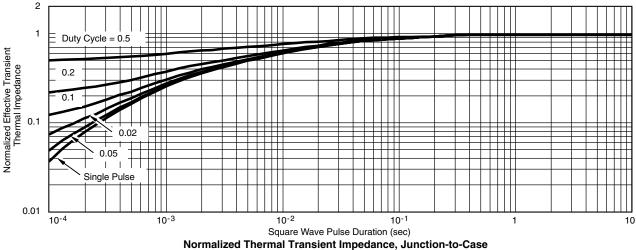


THERMAL RATINGS



Maximum Avalanche Drain Current vs. Case Temperature





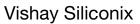
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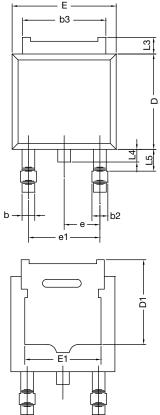
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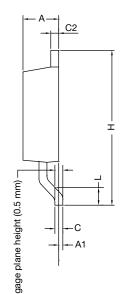
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**TO-252AA Case Outline** 





	MILLIN	IETERS	INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
А	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090 BSC		
e1	4.56	BSC	0.180	BSC	
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T16- DWG: 534	0236-Rev. P, <sup>-</sup> 7	16-May-16			

Notes

• Dimension L3 is for reference only.



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### **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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